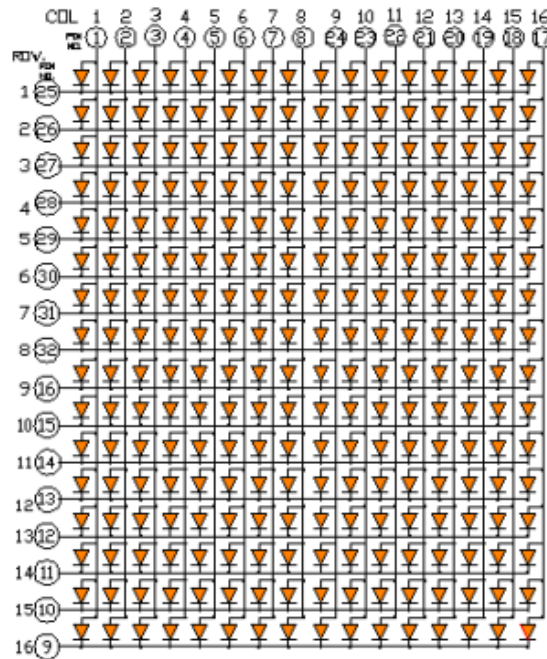


Internal Circuit Diagram



CODE M

Notes:

- All dimensions are in millimeter (inch);
- Tolerance is  $\pm 0.25\text{mm}$  ( $0.01''$ ) especially other specified;
- Pin length, housing color, marking no & circuit diagram can be customized;
- Specifications are subject to change without notice.

**Chip Material: AlGaInP / GaAs Soft Orange LED Chip****Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Maximum Rating	Unit
Power Dissipation	PD	60	mW
Peak Forward Current (1/10 Duty Cycle, 0.1 Ms Pulse Width)	IPEAK	160	mA
DC Forward Current	IF	25	mA
Reverse Voltage	VR	5	V
Operating Temperature Range	TA	-40°C to +85°C	
Storage Temperature Range	TSTG	-40°C to +85°C	
Solder temperature 1/16 inch below seating plane for 3 seconds at 260°C			

**Electrical Optical Character and Curves (Ta=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Location	Test Condition
Forward Voltage	VF	-	2.10	2.40	V	Per Chip	IF=20mA
Luminous Intensity	IV	85.0	90.0	95.0	mcd	Per Chip	IF=20mA
Peak Emission Wavelength	$\lambda_p$	-	610	-	nm	Per Chip	IF=20mA
Dominant Emission Wavelength	$\lambda_d$	600	605	610	nm	Per Chip	IF=20mA
Spectral Line Half-Width	$\Delta\lambda_{1/2}$	-	20	-	nm	Per Chip	IF=20mA
Reverse Current	IR	-	-	10	uA	Per Chip	VR=5V

## Note:

Luminous intensity tolerance is  $\pm 10\%$ ;Dominant Emission Wavelength tolerance is  $\pm 5\%$ .

**Typical Electro-Optical Characteristic Curve:**

FIG. 1 Forward Current vs. Forward Voltage

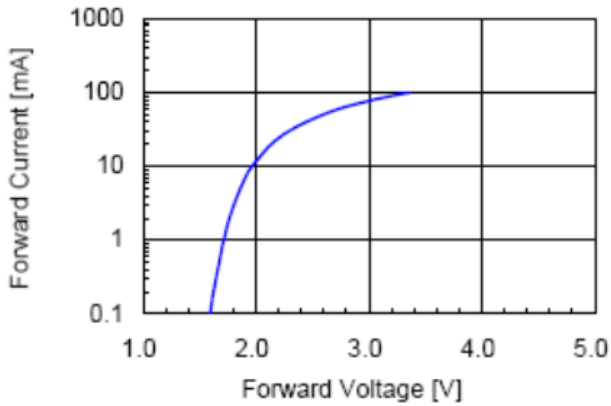


FIG. 2 Relative Intensity Vs. Forward Current

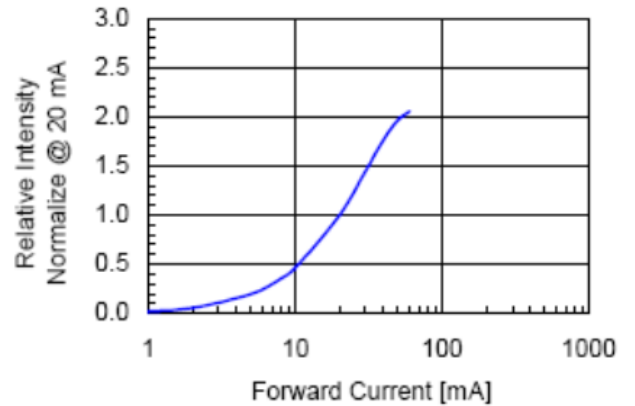


FIG. 3 Forward Voltage vs. Temperature

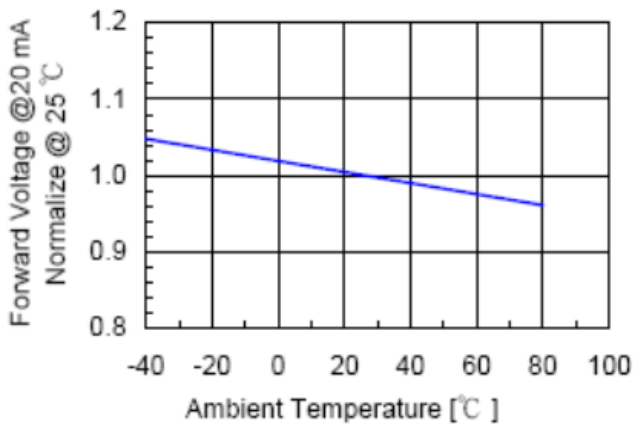


FIG. 4 Relative Intensity vs. Temperature

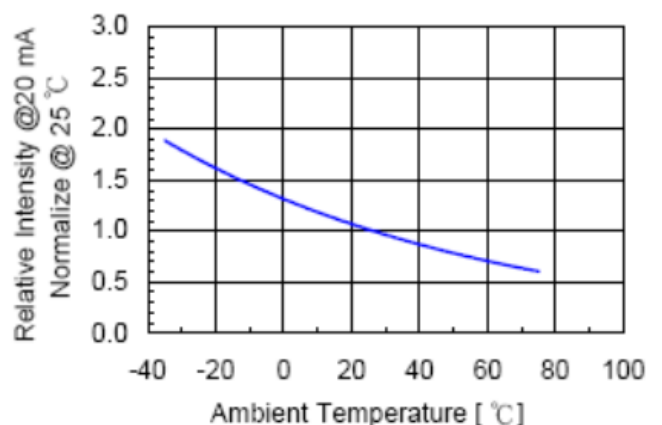


FIG. 5 Relative Intensity vs. Wavelength

